

**CB-FET**

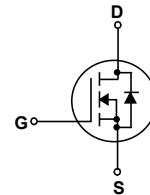
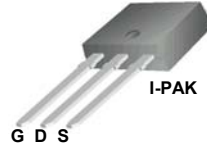
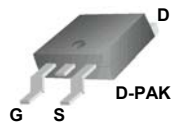
SLD65R2K6SJ / SLU65R2K6SJ 650V N-Channel MOSFET

General Description

This Power MOSFET is produced using Maple semi's Advanced Super-Junction technology. This advanced technology has been especially tailored to minimize conduction loss, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for AC/DC power conversion in switching mode operation for higher efficiency.

Features

- 2.3A, 650V, $R_{DS(on) typ.} = 2.3\Omega @ V_{GS} = 10V$
- Low gate charge (typical 7nC)
- High ruggedness
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	SLD65R2K6SJ / SLU65R2K6SJ	Units
V_{DSS}	Drain-Source Voltage	650	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	2.3*	A
	- Continuous ($T_C = 100^\circ\text{C}$)	1.4*	A
I_{DM}	Drain Current - Pulsed (Note 1)	6.0*	A
V_{GSS}	Gate-Source Voltage	± 30	V
EAS	Single Pulsed Avalanche Energy (Note 2)	15	mJ
I_{AR}	Avalanche Current (Note 1)	1	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	6	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	25	W
	- Derate above 25°C	0.2	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	SLD65R2K6SJ / SLU65R2K6SJ	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	5	$^\circ\text{C/W}$
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	$^\circ\text{C/W}$

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 uA, T _J =25°C	650	--	--	V
		V _{GS} = 0 V, I _D = 250 uA, T _J =150°C	--	700	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 uA, Referenced to 25°C	--	0.6	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650 V, V _{GS} = 0 V	--	--	1	uA
		V _{DS} = 480 V, T _C = 125°C	--	--	10	uA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 uA	2.5	--	4.5	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 1.15A	--	2.3	2.6	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 1.15 A (Note 4)	--	8	--	S
R _g	Gate resistance	f = 1.0 MHz, Open drain	--	3	--	Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	130	--	pF
C _{oss}	Output Capacitance		--	40	--	pF
C _{rss}	Reverse Transfer Capacitance		--	3	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 400 V, I _D = 1.15A, R _G = 20 Ω (Note 4, 5)	--	18	--	ns
t _r	Turn-On Rise Time		--	40	--	ns
t _{d(off)}	Turn-Off Delay Time		--	50	--	ns
t _f	Turn-Off Fall Time		--	30	--	ns
Q _g	Total Gate Charge	V _{DS} = 480 V, I _D = 2.3A, V _{GS} = 10 V (Note 4, 5)	--	15	--	nC
Q _{gs}	Gate-Source Charge		--	3	--	nC
Q _{gd}	Gate-Drain Charge		--	6	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	2.3	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	6	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.3 A	--	--	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 2.3A,	--	150	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/us (Note 4)	--	1.2	--	uC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 60\text{ mH}, I_{AS} = 1.0\text{ A}, V_{DD} = 150\text{ V}$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 2.3\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Typical Characteristics

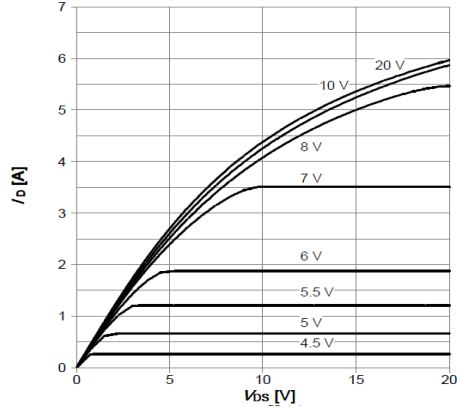


Figure 1: On-Region Characteristics@25°C

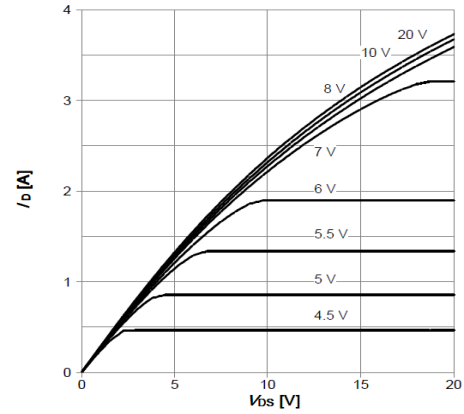


Figure 2: On-Region Characteristics@125°C

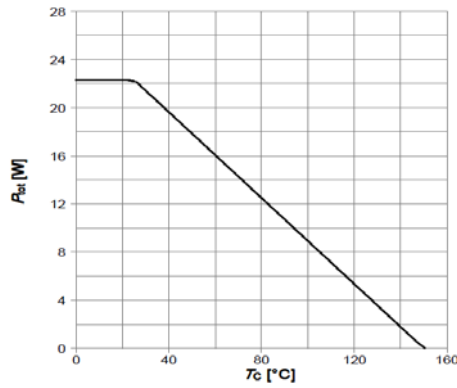


Figure 3: Power Dissipation

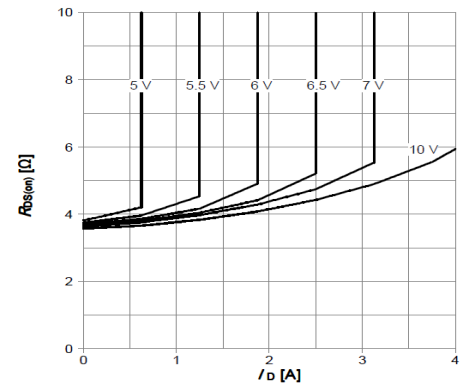


Figure 4: On-Resistance vs. Drain Current and Gate Voltage@125°C

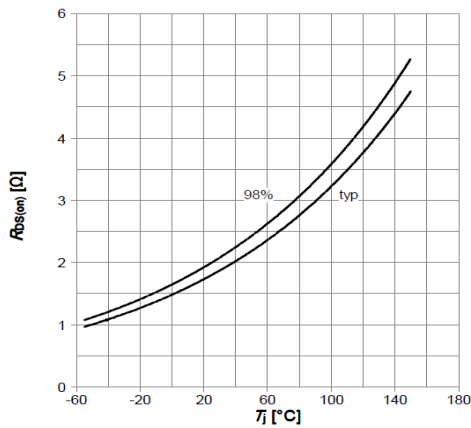


Figure 5: On-Resistance vs. Junction Temperature

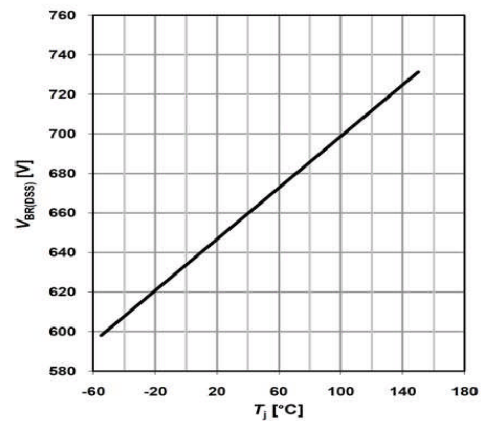


Figure 6: Break Down vs. Junction Temperature

SLD65R2K6SJ / SLU65R2K6SJ

Typical Performance Characteristics

Typical Characteristics

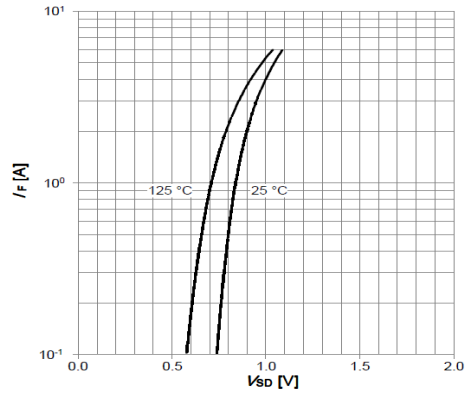


Figure 7: Body-Diode Characteristics

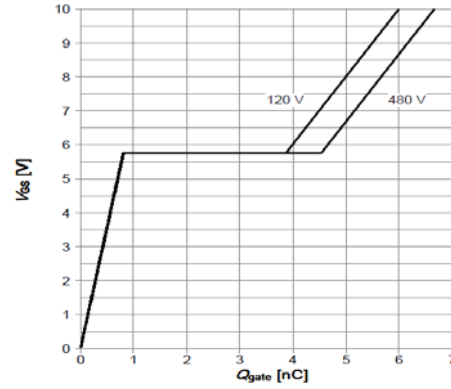


Figure 8: Gate-Charge Characteristics

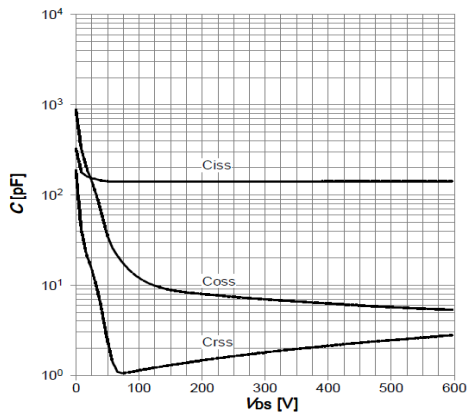


Figure 9: Capacitance Characteristics

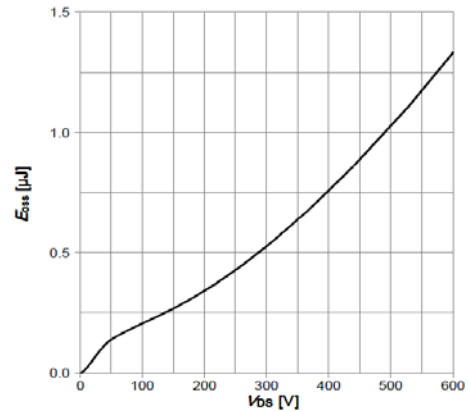


Figure 10: C_{oss} stored Energy

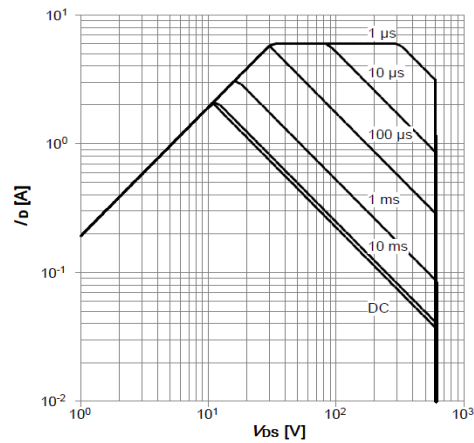


Figure 11: Maximum Forward Biased Safe Operating Area @25°C

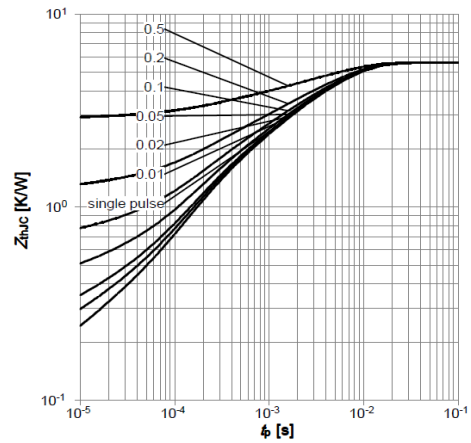


Figure 12: Sing Pulse Power Rating Junction to Case

SLD65R2K6SJ / SLU65R2K6SJ

Typical Characteristics

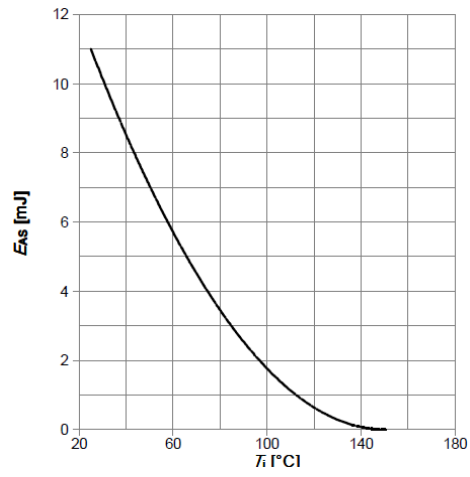


Figure 13: Avalanche energy

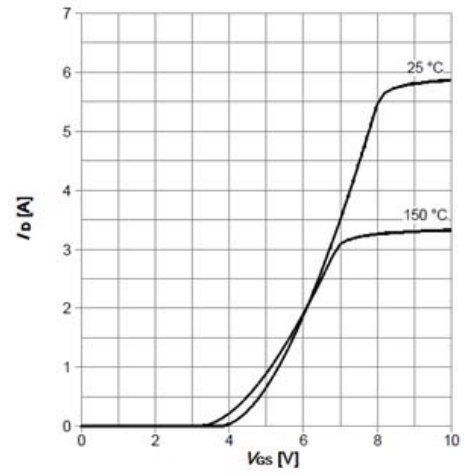
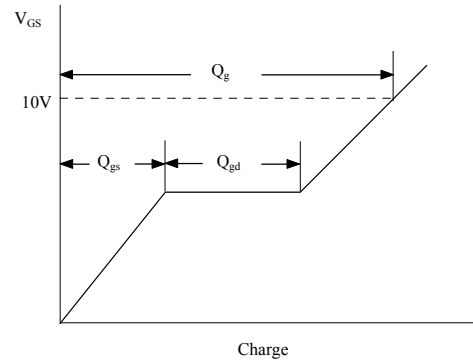
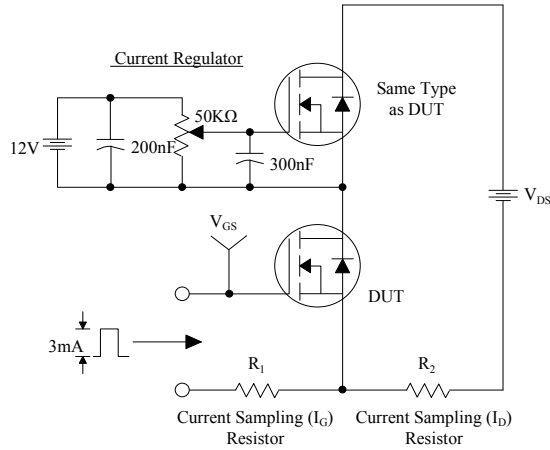
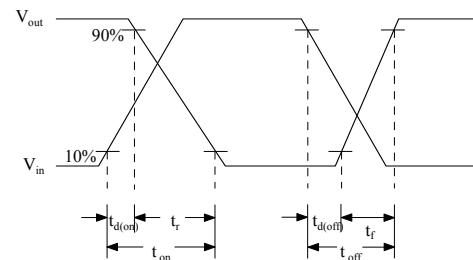
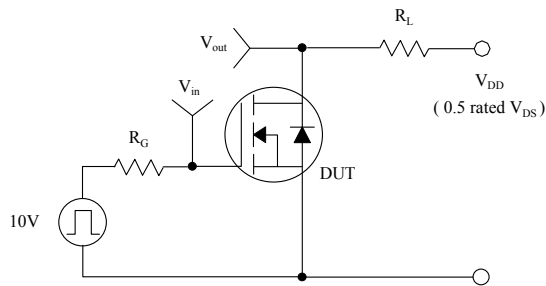


Figure 2: Transfer Characteristics @ $V_{DS}=20V$

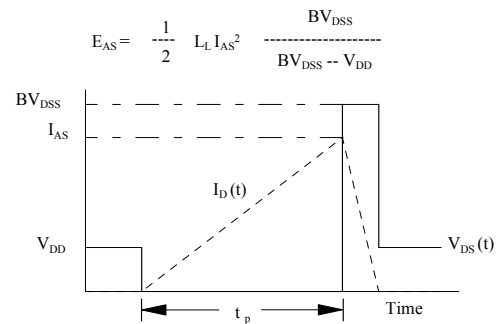
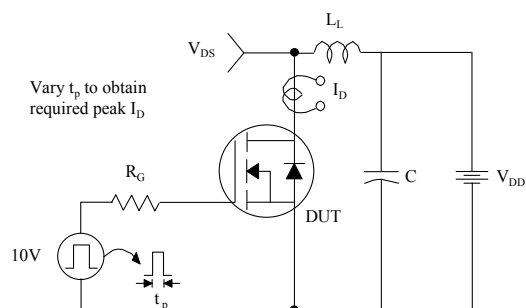
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms

